

Date:- Feb 2004

Data Sheet Issue:- 1

# Provisional Data **Extra Fast Recovery Diode** Type F0800LC180

Old Type No.: F0400LC180

# Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>RRM</sub>	Repetitive peak reverse voltage, (note 1)	1800	V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage, (note 1)	1900	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I <sub>F(AV)M</sub>	Maximum average forward current, T <sub>sink</sub> =55°C, (note 2)	775	A
I <sub>F(AV)M</sub>	Maximum average forward current. T <sub>sink</sub> =85°C, (note 2)	368	А
I <sub>F(AV)M</sub>	Maximum average forward. T <sub>sink</sub> =85°C, (note 3)	210	А
I <sub>F(RMS)</sub>	Nominal RMS forward current, T <sub>sink</sub> =25°C, (note 2)	1545	А
I <sub>f(d.c.)</sub>	D.C. forward current, T <sub>sink</sub> =25°C, (note 4)	1304	А
I <sub>FSM</sub>	Peak non-repetitive surge $t_p$ =10ms, $V_{RM}$ =60% $V_{RRM}$ , (note 5)	7630	A
I <sub>FSM2</sub>	Peak non-repetitive surge $t_p$ =10ms, $V_{RM}$ ≤10V, (note 5)	8400	А
l²t	$I^{2}t$ capacity for fusing t <sub>p</sub> =10ms, V <sub>RM</sub> =60%V <sub>RRM</sub> , (note 5)	291×10 <sup>3</sup>	A <sup>2</sup> s
l²t	$I^{2}t$ capacity for fusing $t_{p}\text{=}10\text{ms},V_{\text{RM}}\text{\leq}10\text{V},(\text{note 5})$	353×10 <sup>3</sup>	A <sup>2</sup> s
T <sub>j op</sub>	Operating temperature range	-40 to +125	°C
T <sub>stg</sub>	Storage temperature range	-40 to +150	°C

Notes:-

- 1) De-rating factor of 0.13% per °C is applicable for  $T_j$  below 25°C.
- 2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
- 3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave,  $125^{\circ}C T_{j}$  initial.
- 6) Current (I<sub>F</sub>) ratings have been calculated using  $V_{T0}$  and  $r_T$  (see page 2).

# **Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V <sub>FM</sub>	Maximum peak forward voltage	-	-	2.05 2.60	I <sub>FM</sub> =800A I <sub>FM</sub> =1600A	V
V <sub>T0</sub> r <sub>T</sub>	Threshold voltage Slope resistance	-	-	1.494 0.692	Current range 775A-2325A (Note 2)	V mΩ
V <sub>T01</sub> r <sub>T1</sub>	Threshold voltage Slope resistance	-	-	1.498 0.690	Current range 800A-2400A	V mΩ
V <sub>FRM</sub>	Maximum forward recovery voltage	-	-	82 68	di/dt = 1000A/µs di/dt = 1000A/µs, Tj=25°C	V
I <sub>RRM</sub>	Peak reverse current	-	-	150 30	Rated V <sub>RRM</sub> Rated V <sub>RRM</sub> , T <sub>j</sub> =25°C	mA
Q <sub>ra</sub> t <sub>rr</sub> I <sub>rm</sub>	Recovered charge, 50% Chord Reverse recovery time, 50% Chord Reverse recovery current	- - -	200 1.1 380		I <sub>FM</sub> =800A, t <sub>p</sub> =500µs, di/dt=1000A/µs, V <sub>r</sub> =500V, 50% Chord. (note 3)	μC μs A
Q <sub>ra</sub> t <sub>rr</sub> I <sub>rm</sub>	Recovered charge, 50% Chord Reverse recovery time, 50% Chord Reverse recovery current	- - -	55 1.0 120	65 - -	I <sub>FM</sub> =1000A, t <sub>p</sub> =500μs, di/dt=200A/μs, V <sub>r</sub> =50V, 50% Chord.	μC μs A
R <sub>thJK</sub>	Thermal resistance, junction to heatsink	-	-	0.032 0.064	Double side cooled Single side cooled	K/W
F Wt	Mounting force Weight	10 -	- 340	20 -		kN g

#### Notes:-

- Unless otherwise indicated T<sub>j</sub>=125°C.
  V<sub>T0</sub> and r<sub>T</sub> were used to calculate the current ratings illustrated on page one.
  Figures 3-6 were compiled using these conditions.
- 4) For other clamp forces consult factory.

#### Notes on Ratings and Characteristics

# 1.0 Voltage Grade Table

Voltage Grade	V <sub>RRM</sub>	V <sub>RSM</sub>	V <sub>R</sub> dc
	(V)	(V)	(V)
18	1800	1900	900

#### 2.0 De-rating Factor

A blocking voltage de-rating factor of 0.13% per °C is applicable to this device for T<sub>j</sub> below 25°C.

#### 3.0 ABCD Constants

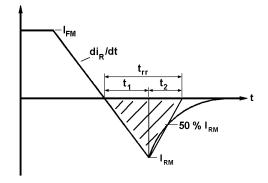
These constants (applicable only over current range of  $V_F$  characteristic in Figure 1) are the coefficients of the expression for the forward characteristic given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

where  $I_F$  = instantaneous forward current.

#### 4.0 Reverse recovery ratings

(i) Q<sub>ra</sub> is based on 50% I<sub>rm</sub> chord as shown in Fig.(a) below.



(ii)  $Q_{rr}$  is based on a 150µs integration time.

I.e. 
$$Q_{rr} = \int_{0}^{150\,\mu s} i_{rr}.dt$$

(iii) 
$$K Factor = \frac{t_1}{t_2}$$

#### 5.0 Reverse Recovery Loss

The following procedure is recommended for use where it is necessary to include reverse recovery loss.

From waveforms of recovery current obtained from a high frequency shunt (see Note 1) and reverse voltage present during recovery, an instantaneous reverse recovery loss waveform must be constructed. Let the area under this waveform be E joules per pulse. A new sink temperature can then be evaluated from:

$$T_{SINK} = T_{J(MAX)} - E \cdot \left[k + f \cdot R_{thJK}\right]$$

Where k = 0.2314 (°C/W)/s

*E* = Area under reverse loss waveform per pulse in joules (W.s.)

f = Rated frequency in Hz at the original sink temperature.

 $R_{thJK}$  = d.c. thermal resistance (°C/W)

The total dissipation is now given by:

$$W_{(tot)} = W_{(original)} + E \cdot f$$

NOTE 1 - Reverse Recovery Loss by Measurement

This device has a low reverse recovered charge and peak reverse recovery current. When measuring the charge, care must be taken to ensure that:

(a) AC coupled devices such as current transformers are not affected by prior passage of high amplitude forward current.

(b) A suitable, polarised, clipping circuit must be connected to the input of the measuring oscilloscope to avoid overloading the internal amplifiers by the relatively high amplitude forward current signal.

(c) Measurement of reverse recovery waveform should be carried out with an appropriate critically damped snubber, connected across diode anode to cathode. The formula used for the calculation of this snubber is shown below:

$$R^2 = 4 \cdot \frac{V_r}{C_s \cdot \frac{di}{dt}}$$

Where: V<sub>r</sub> = Commutating source voltage

- $C_{S}$  = Snubber capacitance
- R = Snubber resistance

#### 6.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

#### 7.0 Computer Modelling Parameters

7.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_o + \sqrt{V_o + 4 \cdot ff^2 \cdot r_s \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_s}$$

Where  $V_{T0} = 1.494$ V,  $r_T = 0.692$ m $\Omega$ 

ff = form factor (normally unity for fast diode applications)

$$W_{AV} = \frac{\Delta T}{R_{th}}$$
$$\Delta T = T_{j(MAX)} - T_{H}$$

7.2 Calculation of VF using ABCD Coefficients

K

The forward characteristic IF Vs VF, on page 6 is represented in two ways;

- the well established V<sub>0</sub> and r<sub>s</sub> tangent used for rating purposes and (i)
- (ii) a set of constants A, B, C, and D forming the coefficients of the representative equation for V<sub>F</sub> in terms of I<sub>F</sub> given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given in this report for hot characteristics. The resulting values for V<sub>F</sub> agree with the true device characteristic over a current range, which is limited to that plotted.

	25°C Coefficients	125°C Coefficients
А	0.5500522	-1.3840139
В	0.195326	0.6344428
С	3.6494×10⁻⁴	9.83261×10 <sup>-4</sup>
D	6.89769×10 <sup>-3</sup>	-0.05634619

#### 8.0 Frequency Ratings

The curves illustrated in figures 8 to 16 are for guidance only and are superseded by the maximum ratings shown on page 1.

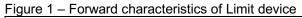
#### 9.0 Square wave ratings

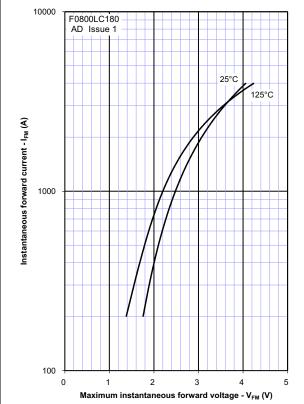
These ratings are given for load component rate of rise of forward current of 100 and 500 A/µs.

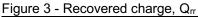
#### 10.0 Duty cycle lines

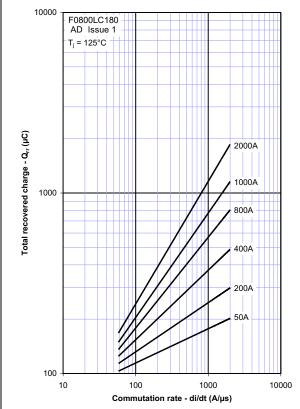
The 100% duty cycle is represented on all the ratings by a straight line. Other duties can be included as parallel to the first.

# **Curves**









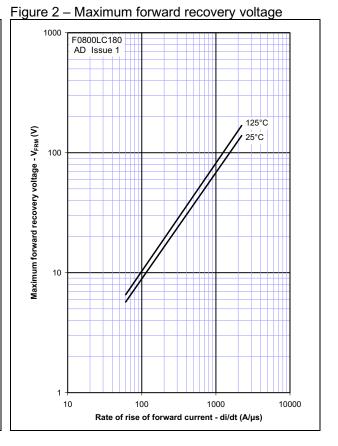
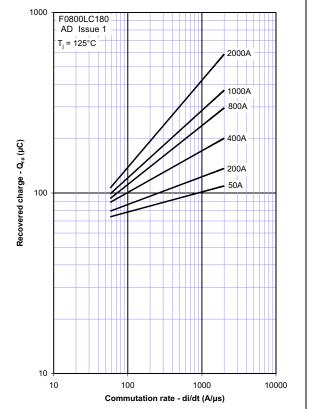
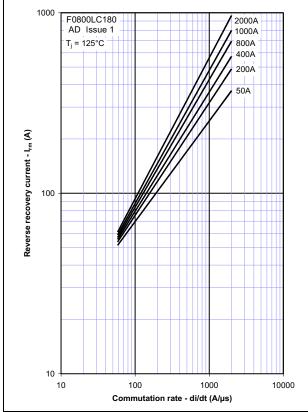
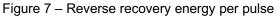


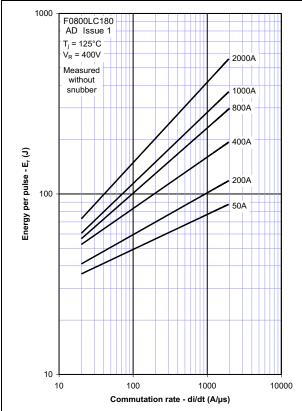
Figure 4 – Recovered charge, Qra (50% chord)



#### Figure 5 - Maximum reverse current, Irm







10 F0800LC180 AD Issue 1 T<sub>j</sub> = 125°C Recovery time - t<sub>rr</sub> (µs) 2000A 1 1000A 800A 400A 200A 50A 0.1 10000 10 1000 100 Commutation rate - di/dt (A/µs)

Figure 8 - Sine wave energy per pulse

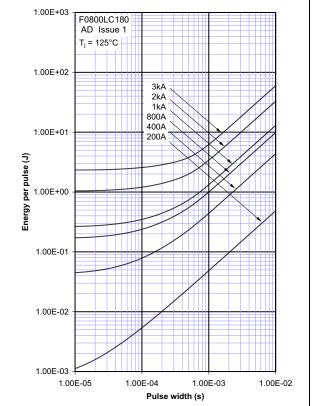
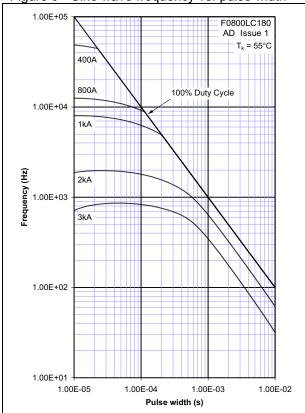
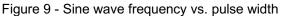
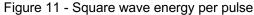
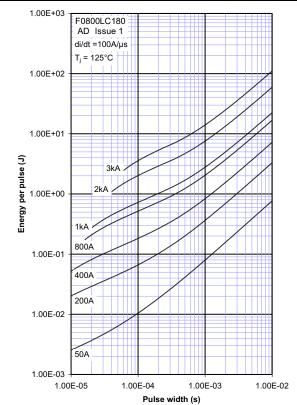


Figure 6 - Maximum recovery time, trr (50% chord)









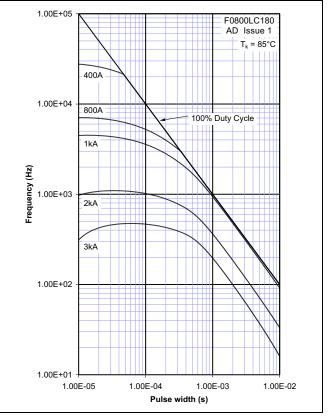


Figure 12 - Square wave energy per pulse

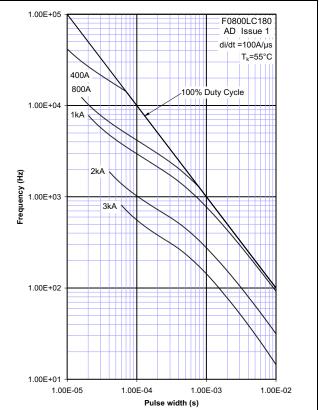


Figure 10 - Sine wave frequency vs. pulse width

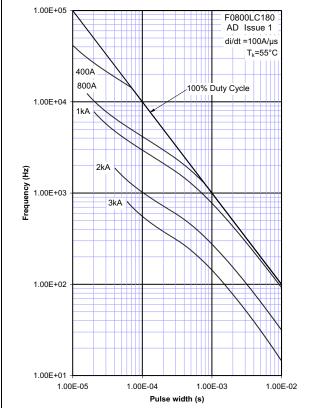
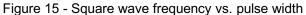
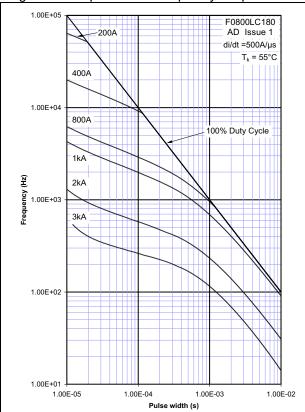


Figure 13 - Square wave frequency vs. pulse width





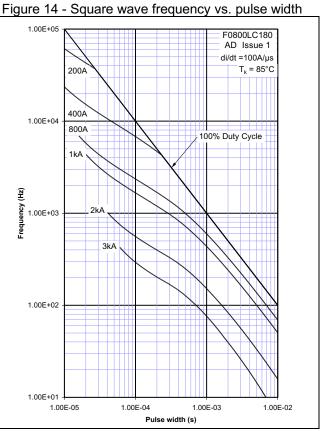
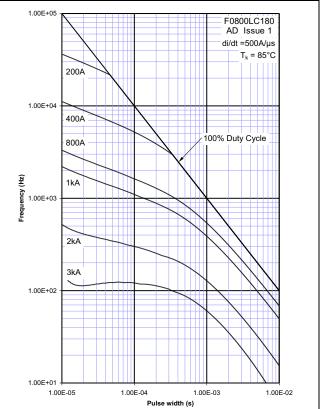
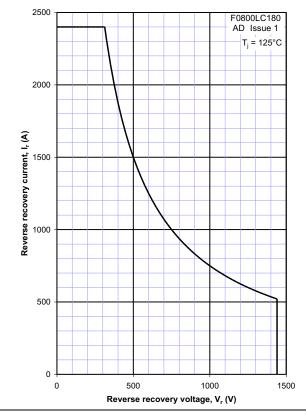


Figure 16 - Square wave frequency vs. pulse width



DSC 0.064K/W

SSC 0.032K/W



# Figure 17 – Safe operating area



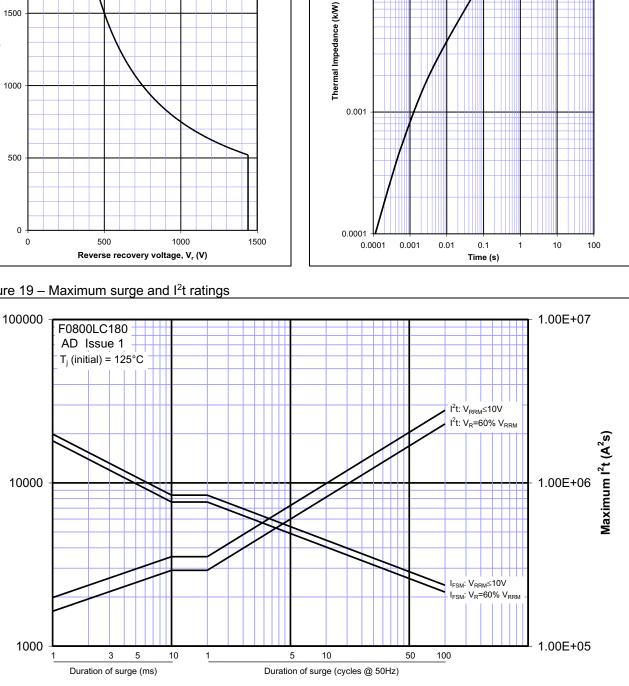


Figure 18 – Transient thermal impedance

F0800LC180

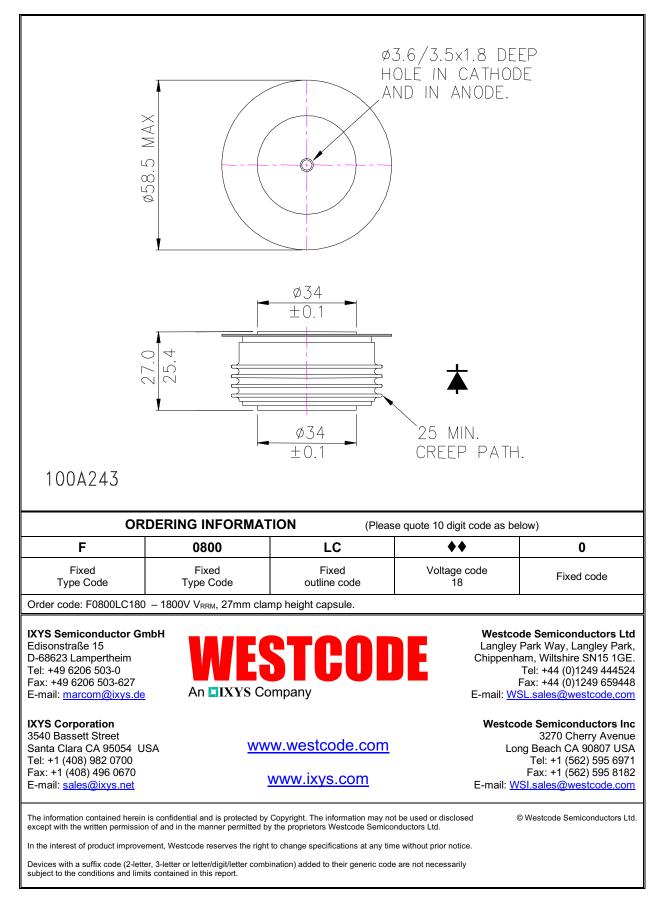
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0.1

0.01

Total peak half sine surge current - I<sub>FSM</sub> (A)

# **Outline Drawing & Ordering Information**





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